

FIG. 1

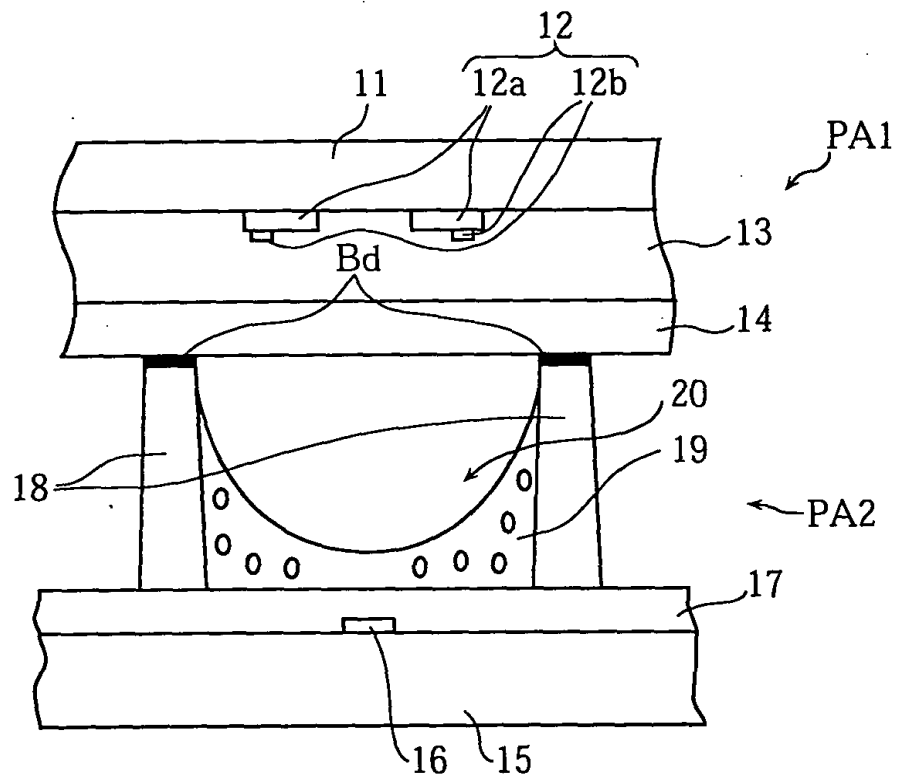


FIG. 2

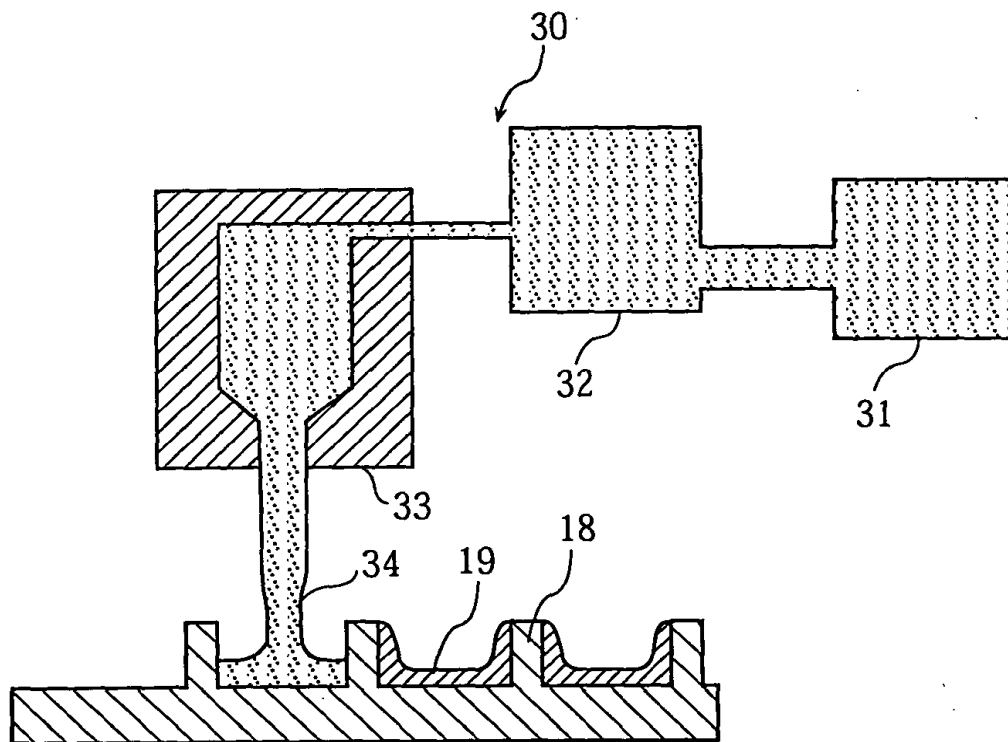


FIG. 3

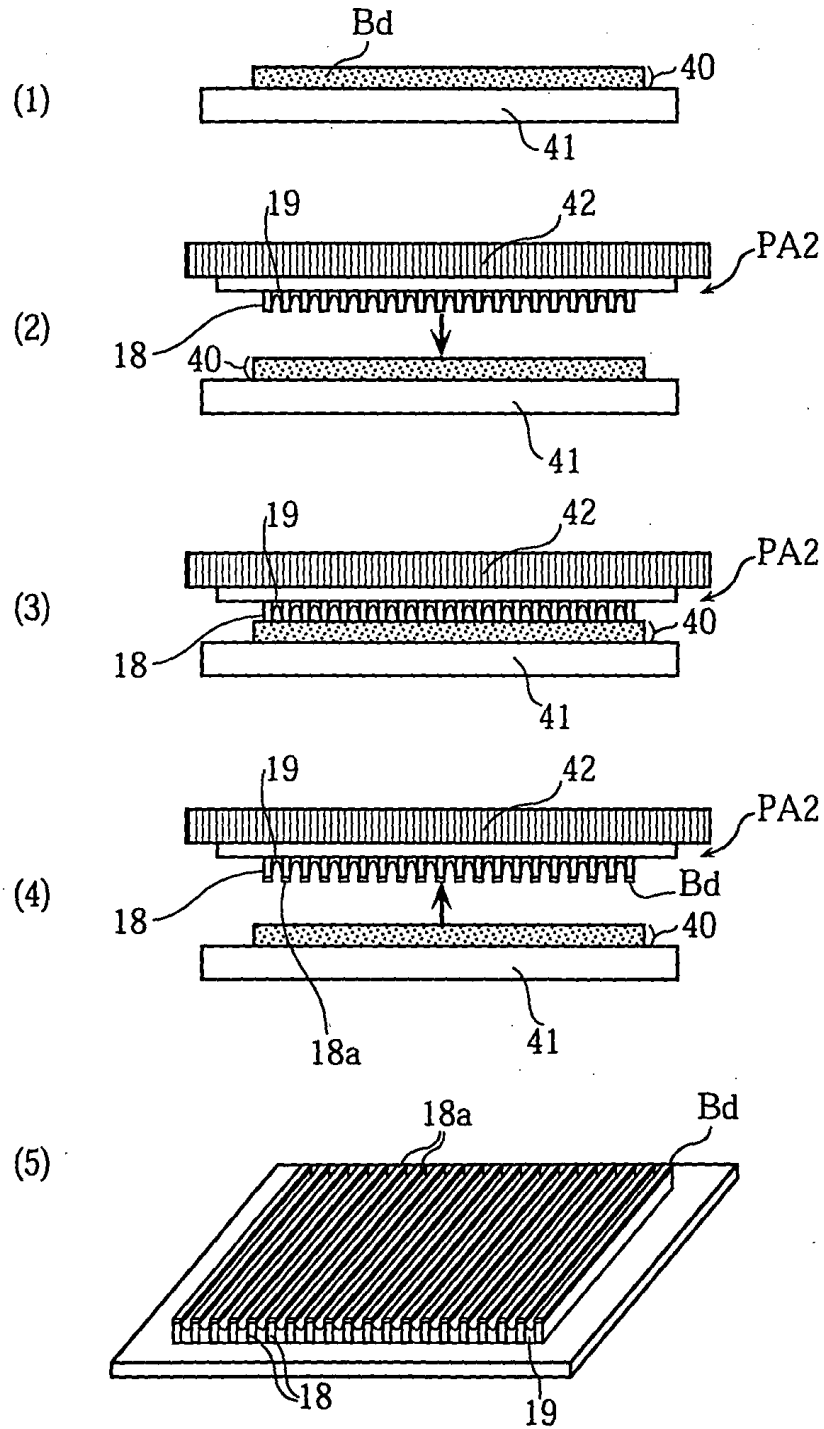


FIG. 4A

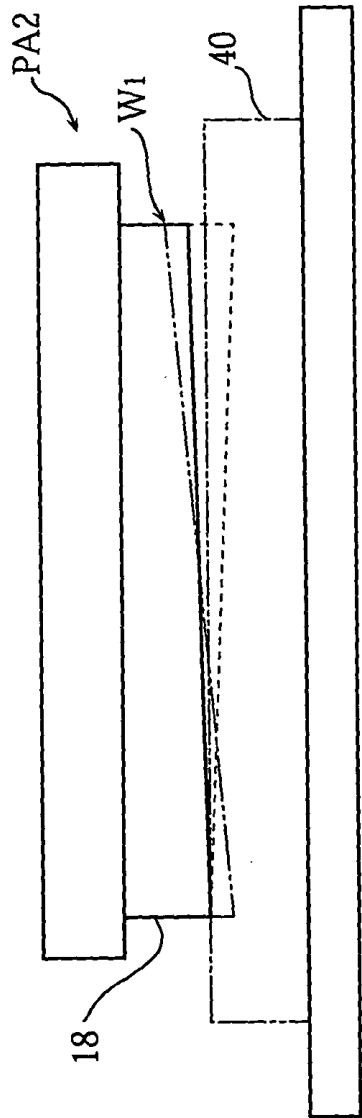


FIG. 4B

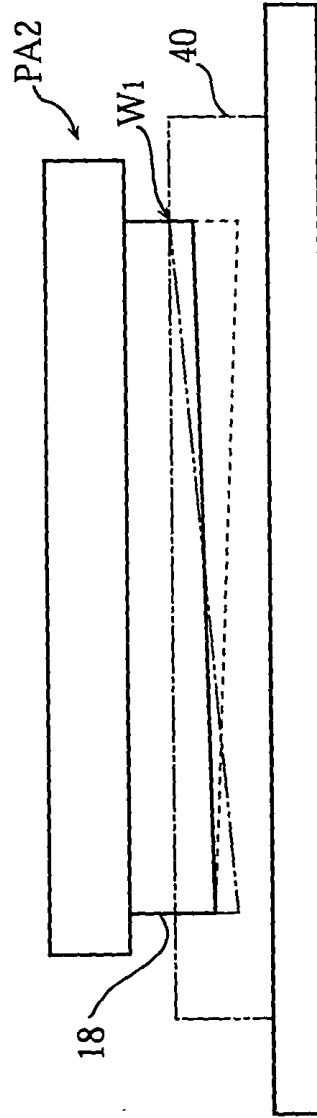


FIG. 5

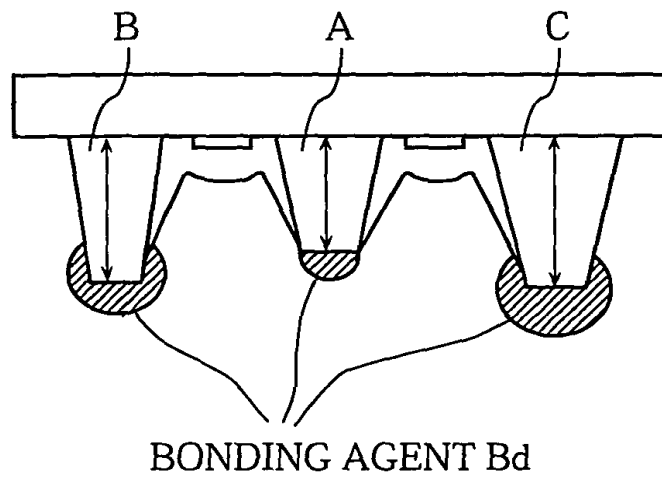


FIG. 6A

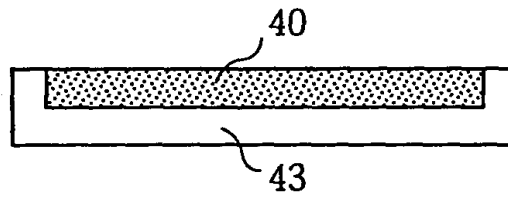


FIG. 6B

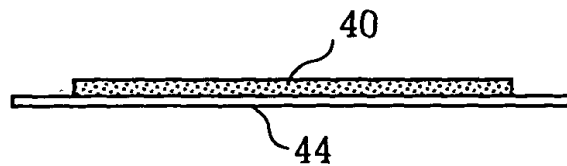


FIG. 7

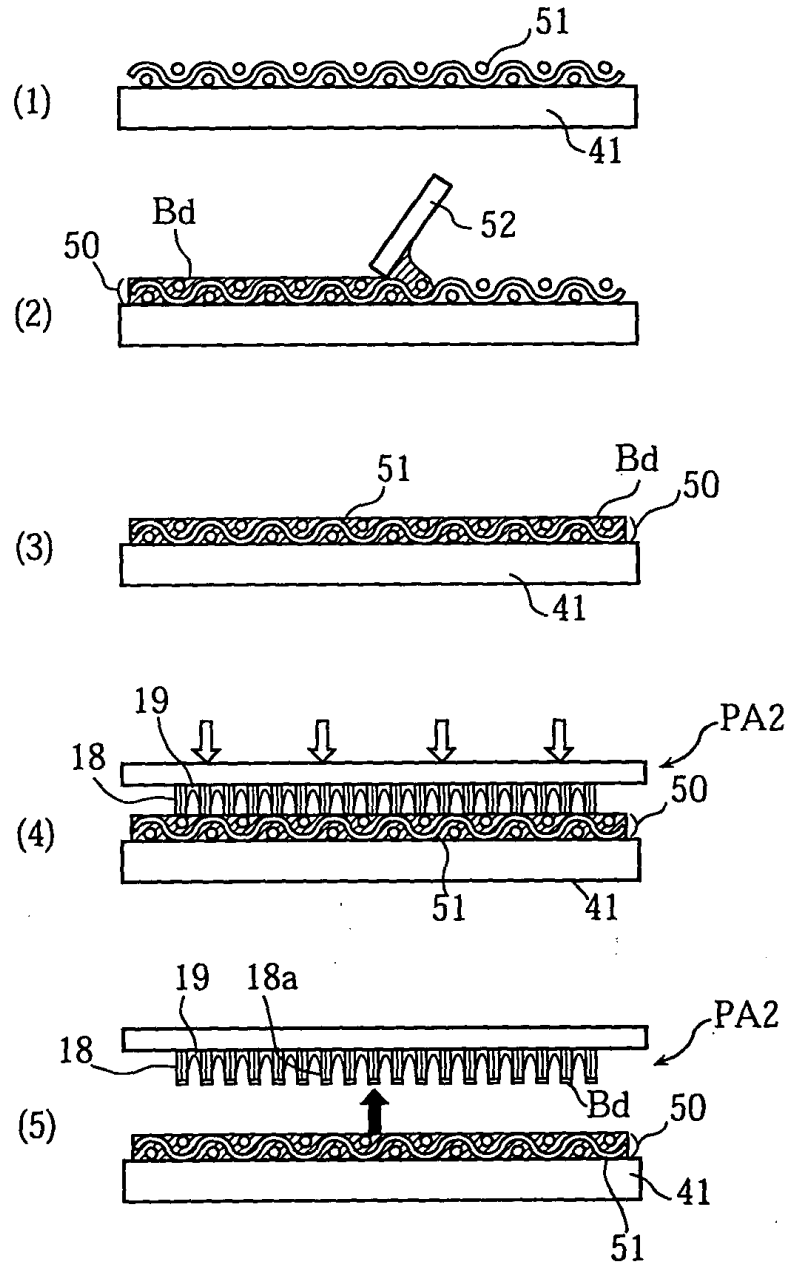


FIG. 8

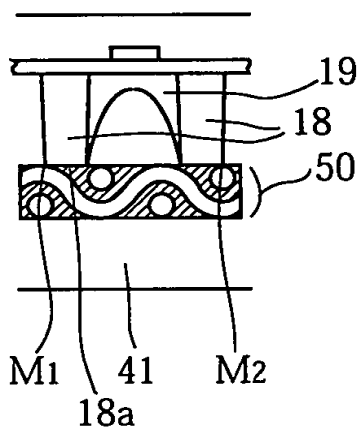


FIG. 9

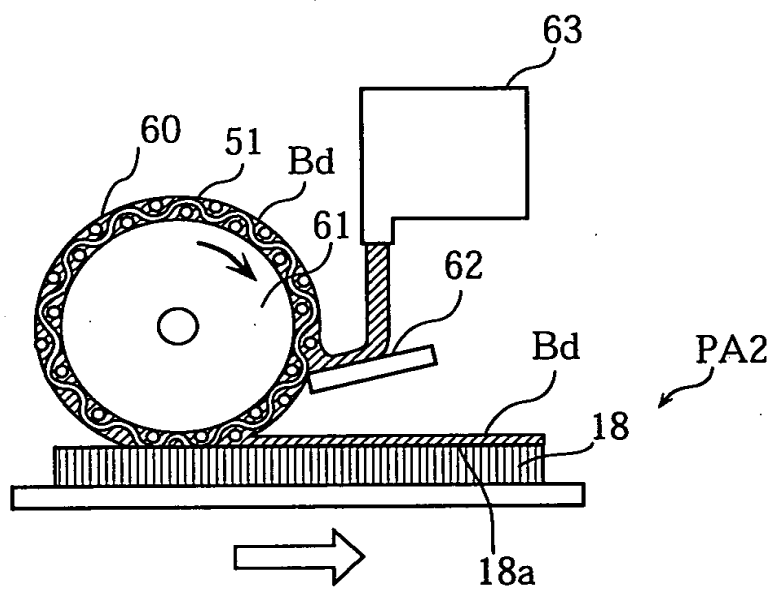


FIG. 10

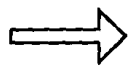
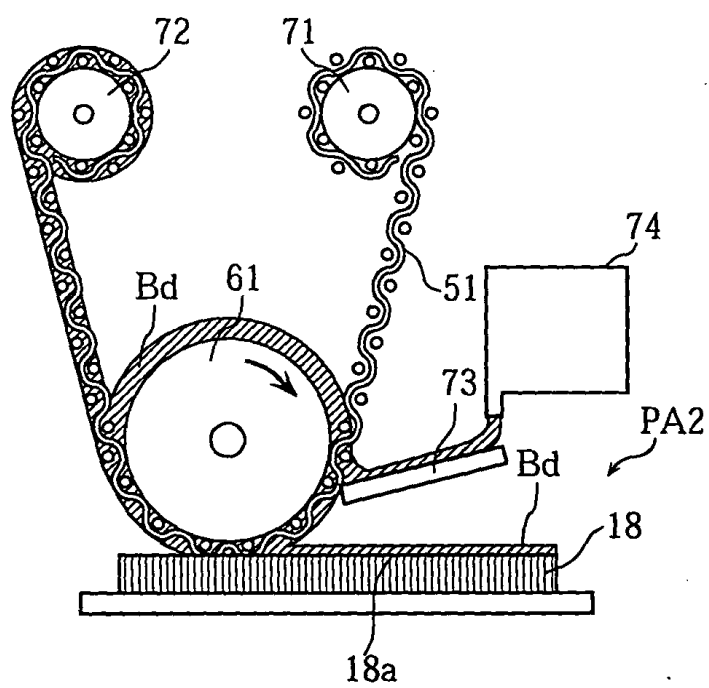


FIG. 11

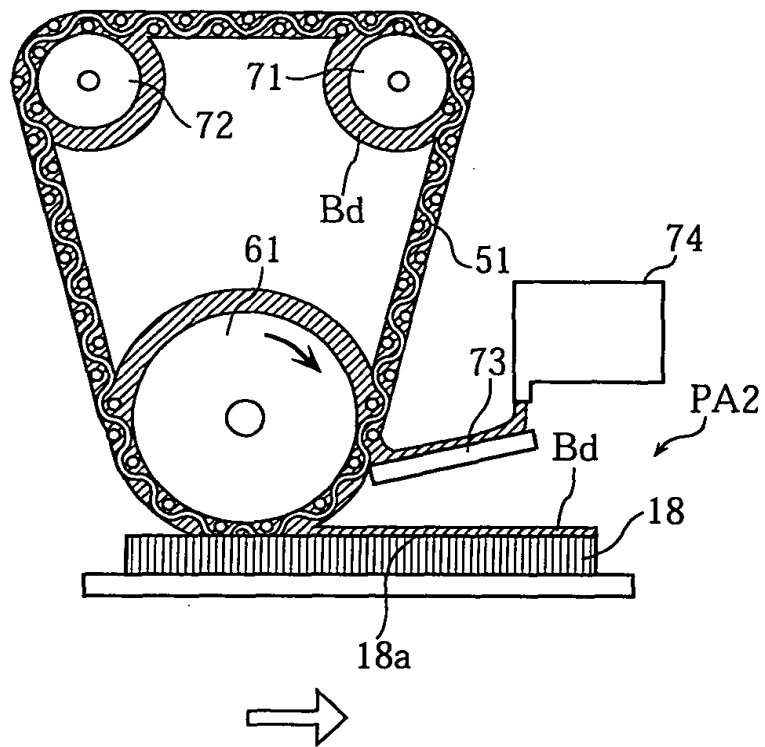


FIG. 12

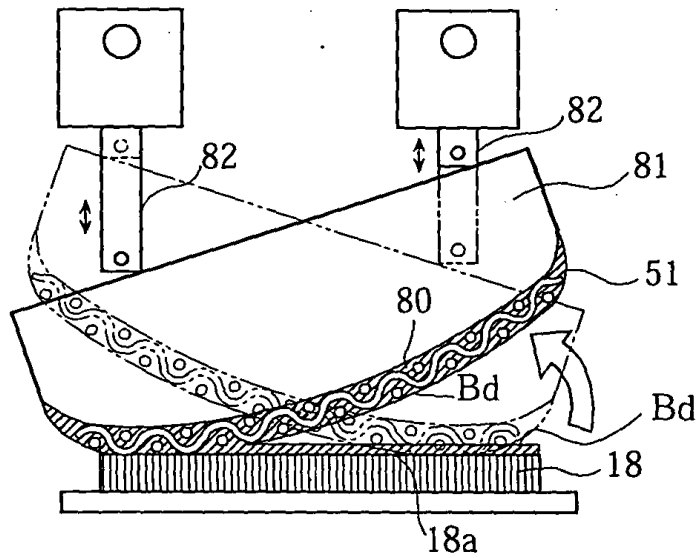
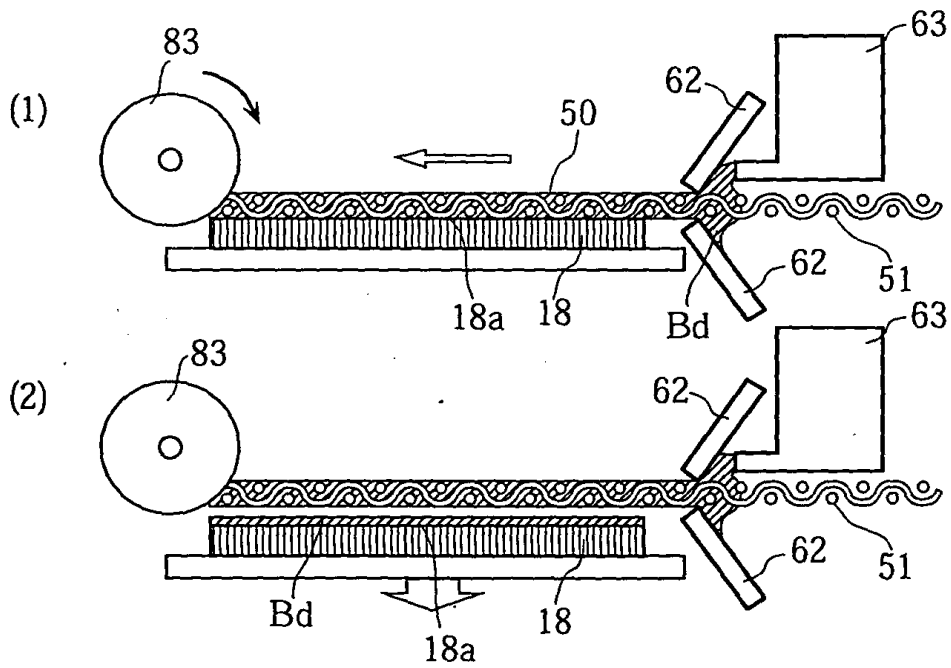


FIG. 13



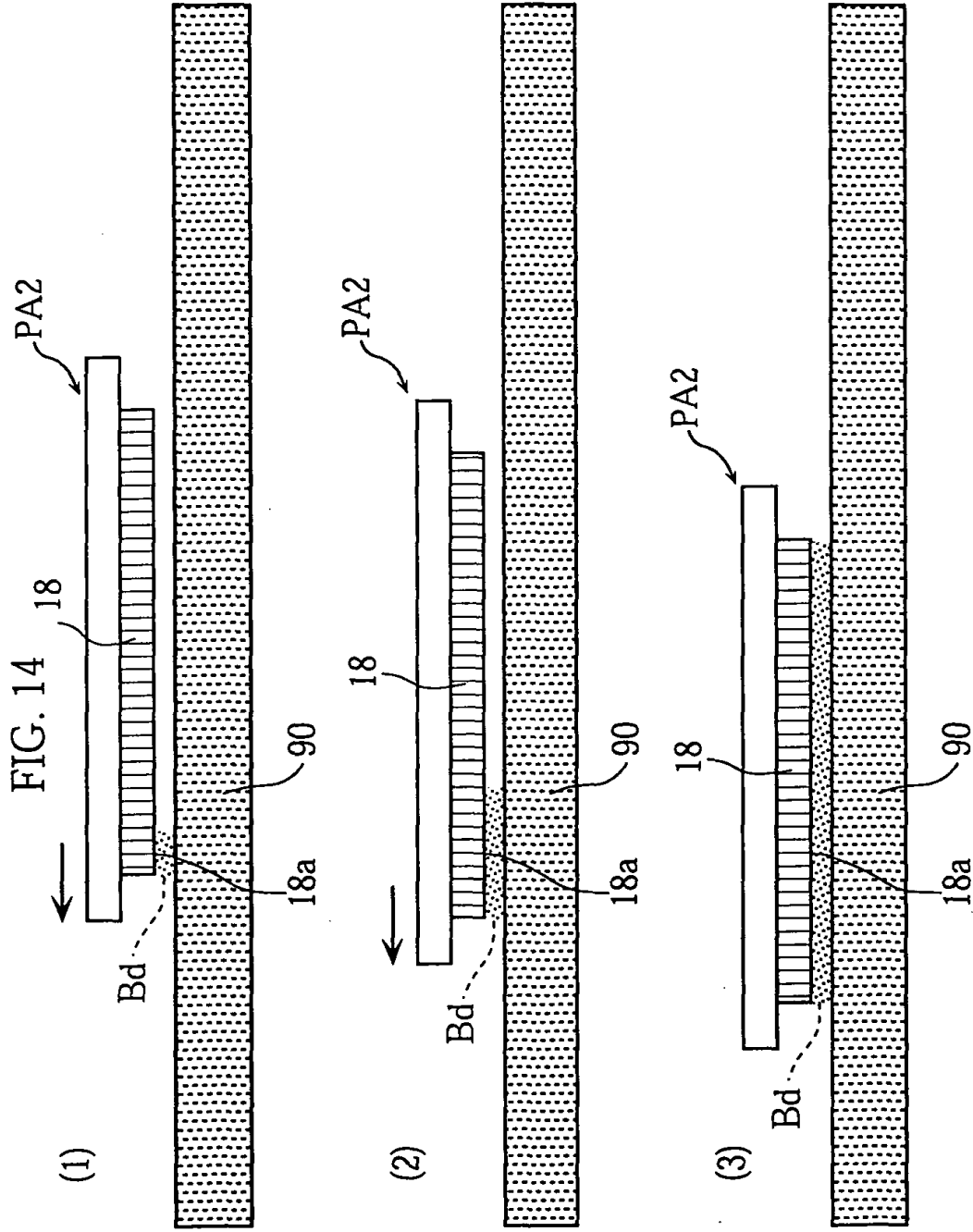


FIG. 15

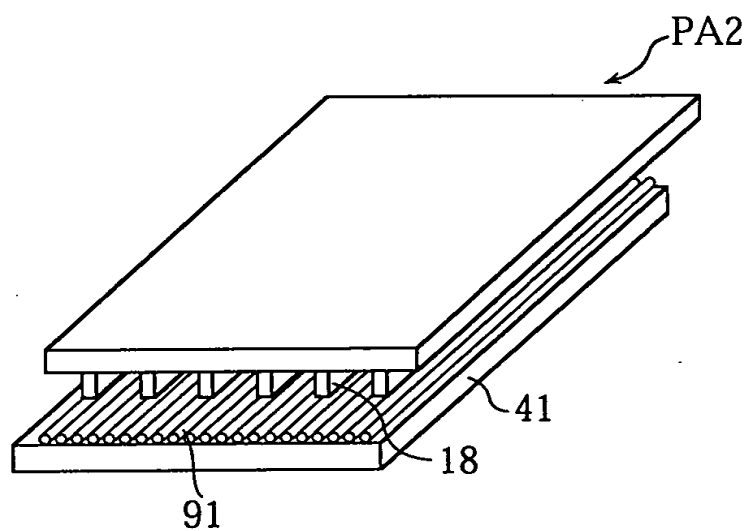


FIG. 16

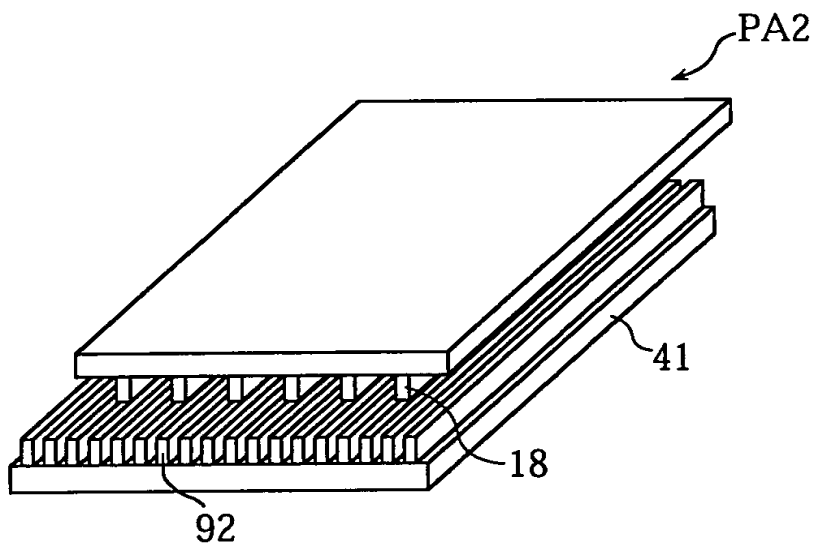


FIG. 17

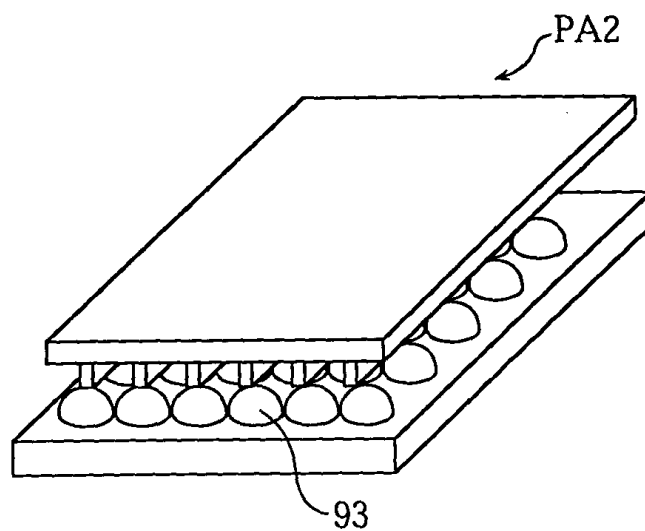


FIG. 18

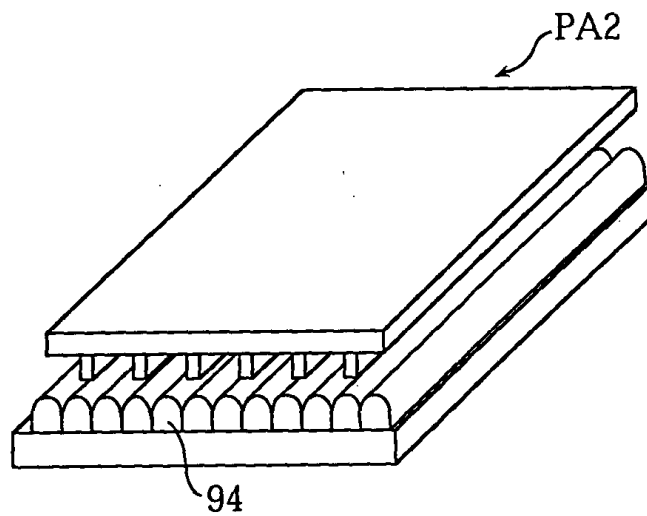


FIG. 19

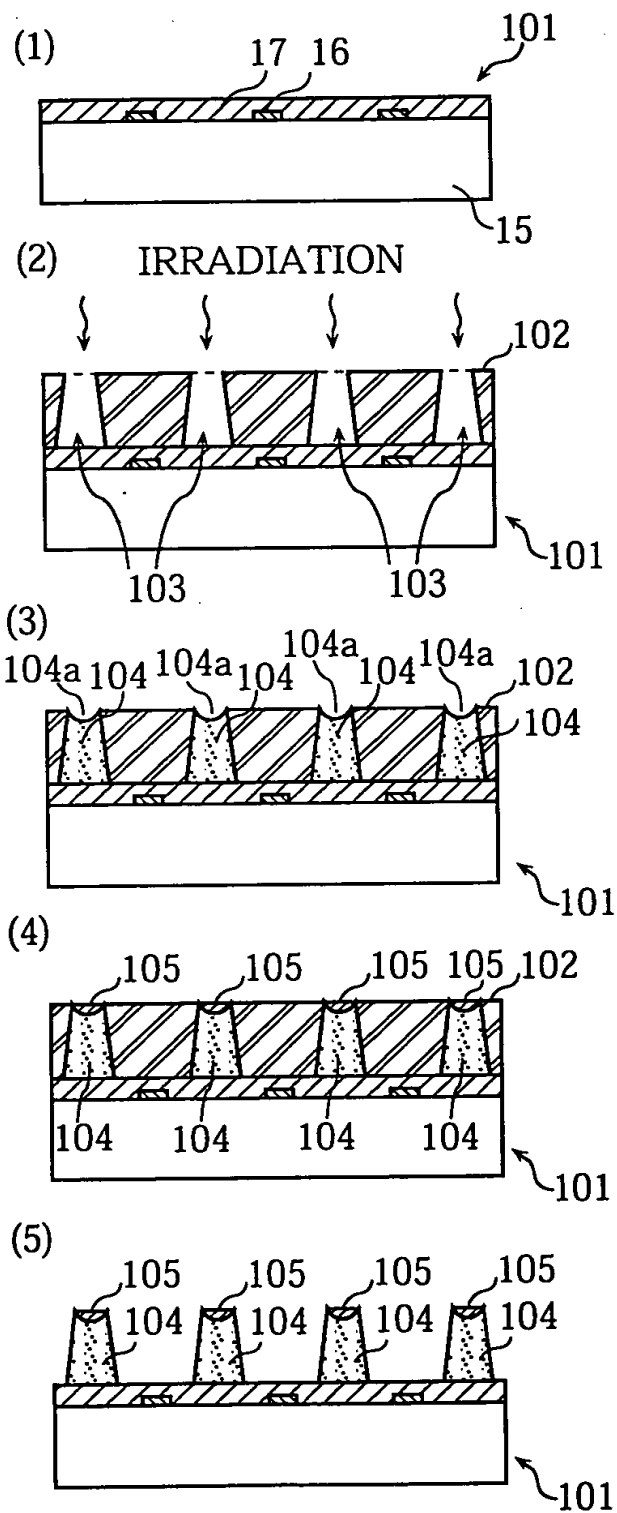


FIG. 20

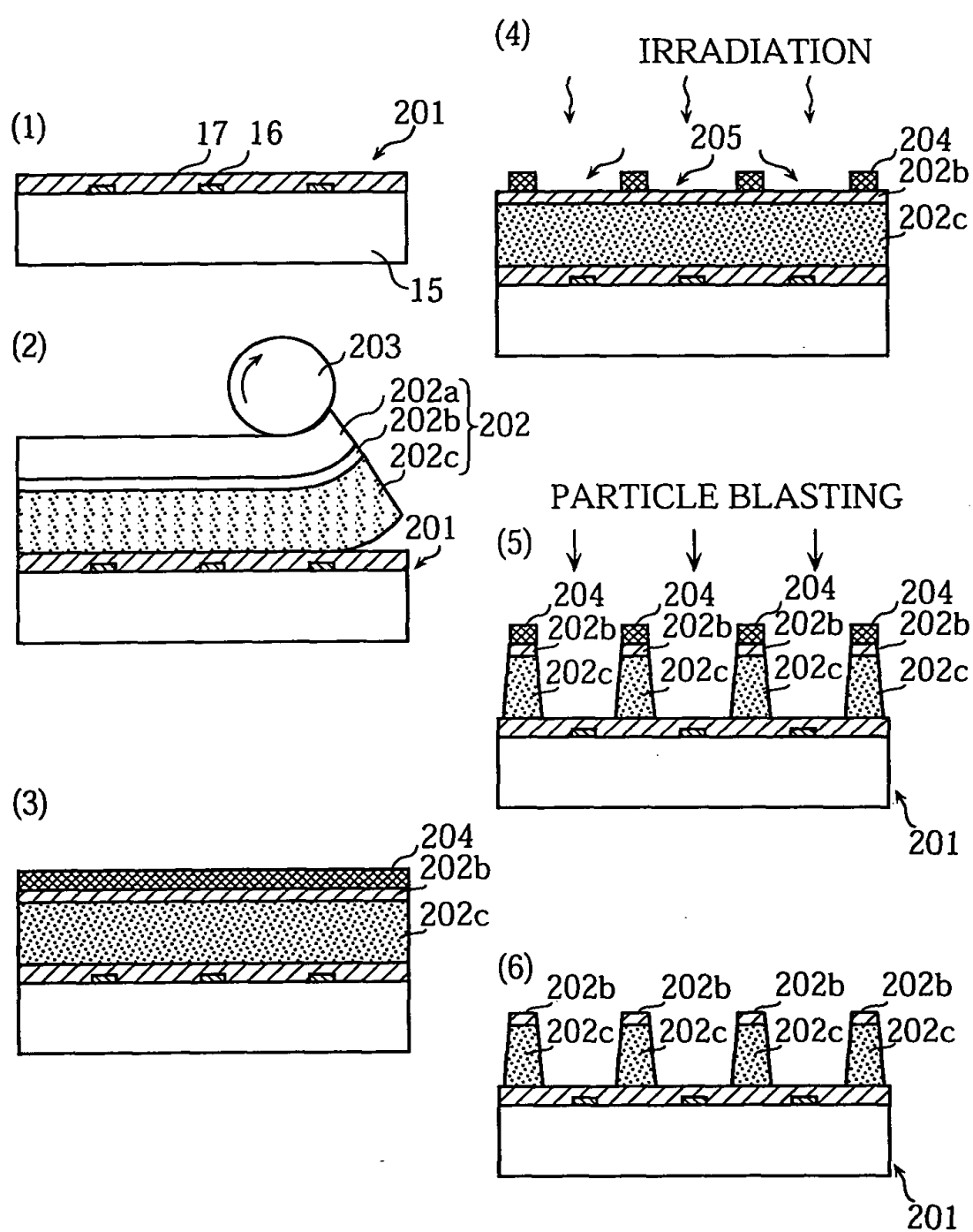


FIG. 21

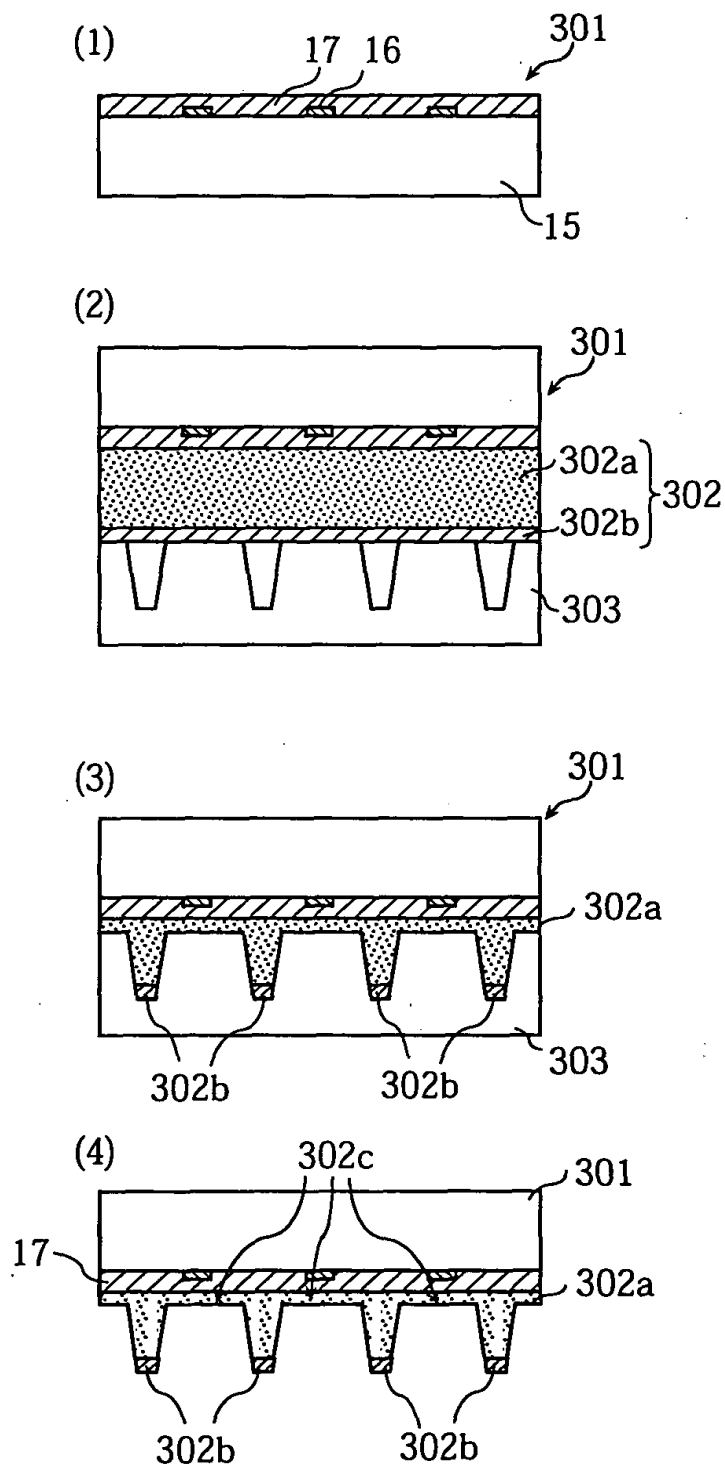


FIG. 22

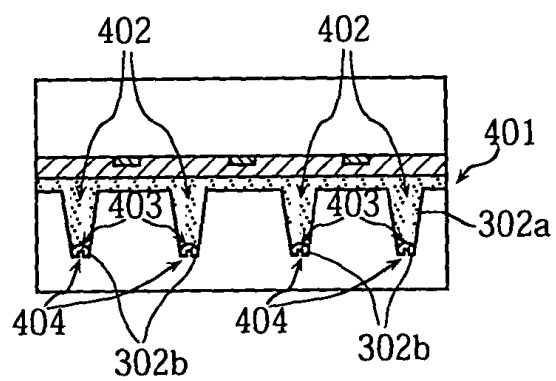


Figure 1 shows five cross-sectional views of a semiconductor device manufacturing process:

- (1) A substrate 15 with a thin layer 16 and particles 17.
- (2) A layer 501 is added, followed by a patterned layer 502 and a layer 503 with openings.
- (3) The layer 503 is filled with a material 502.
- (4) The material 502 is etched back to form a patterned layer 504.
- (5) The patterned layer 504 is further processed to form a final structure 505.

FIG. 24

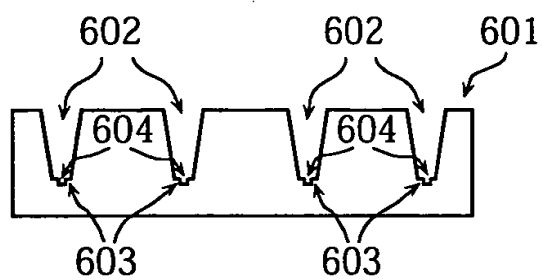


FIG. 25

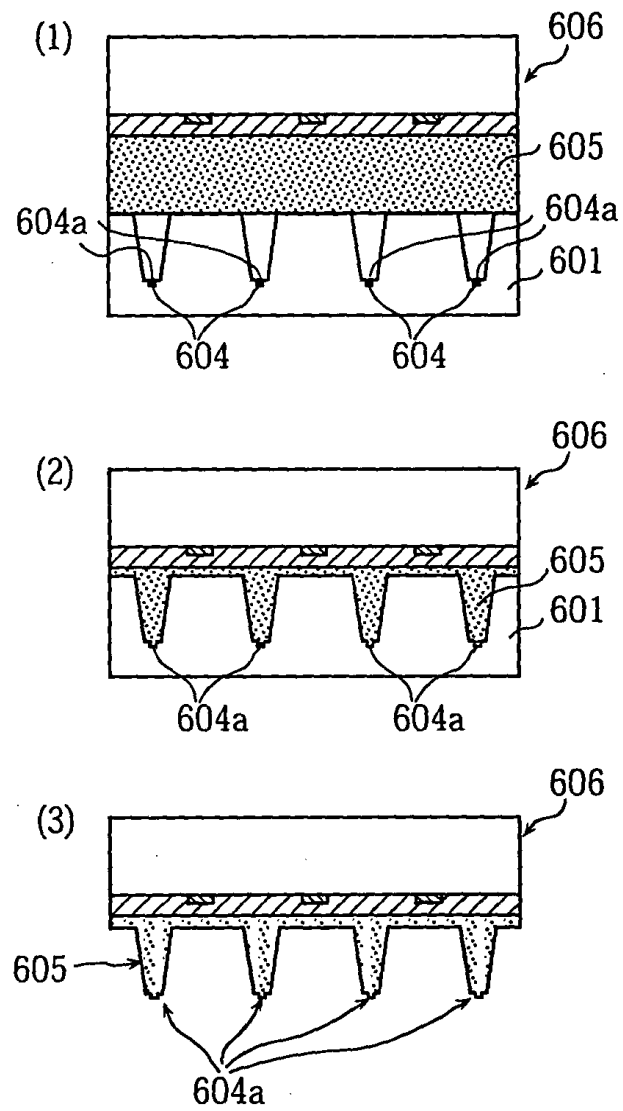


FIG. 26

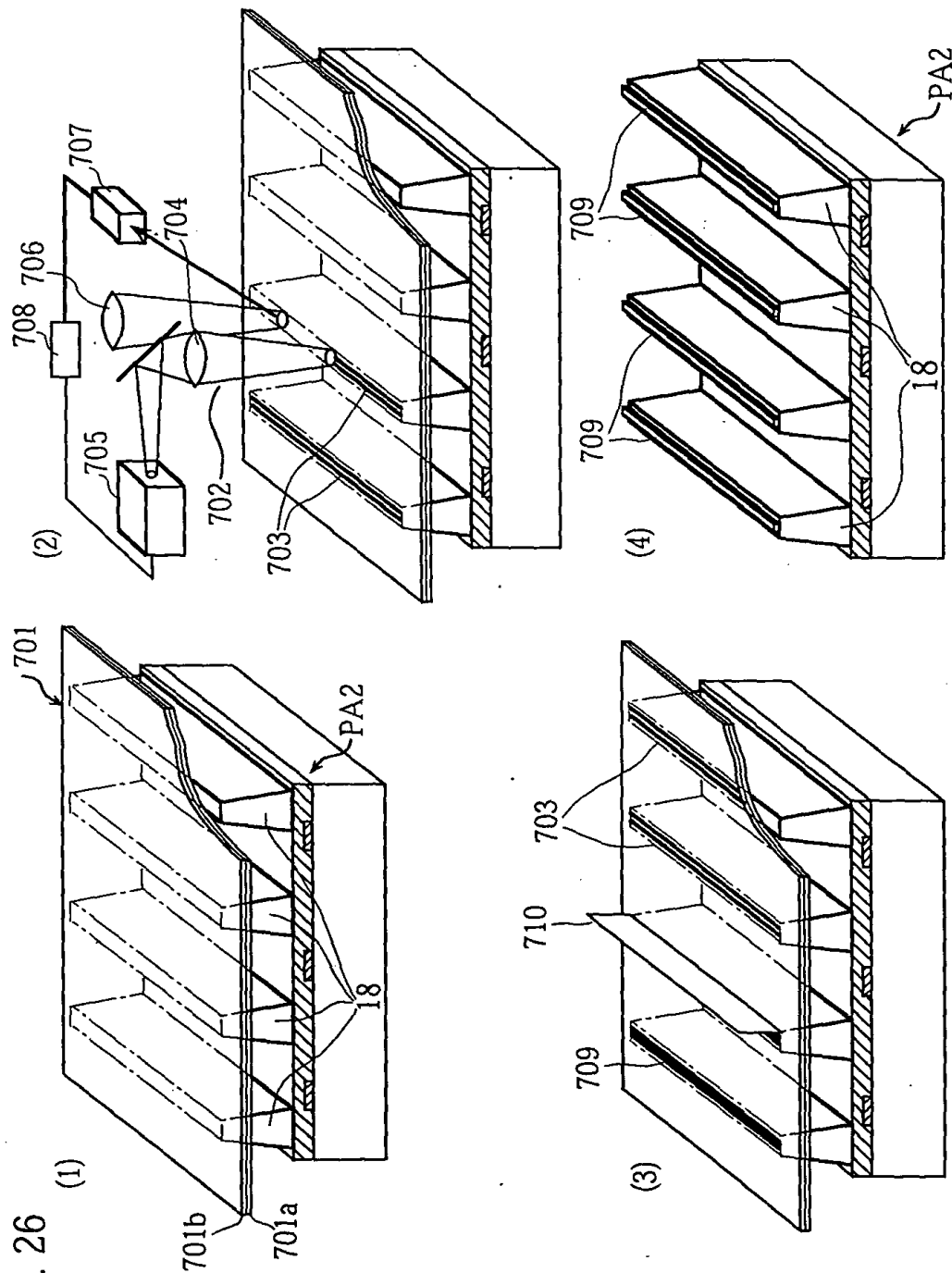


FIG. 27

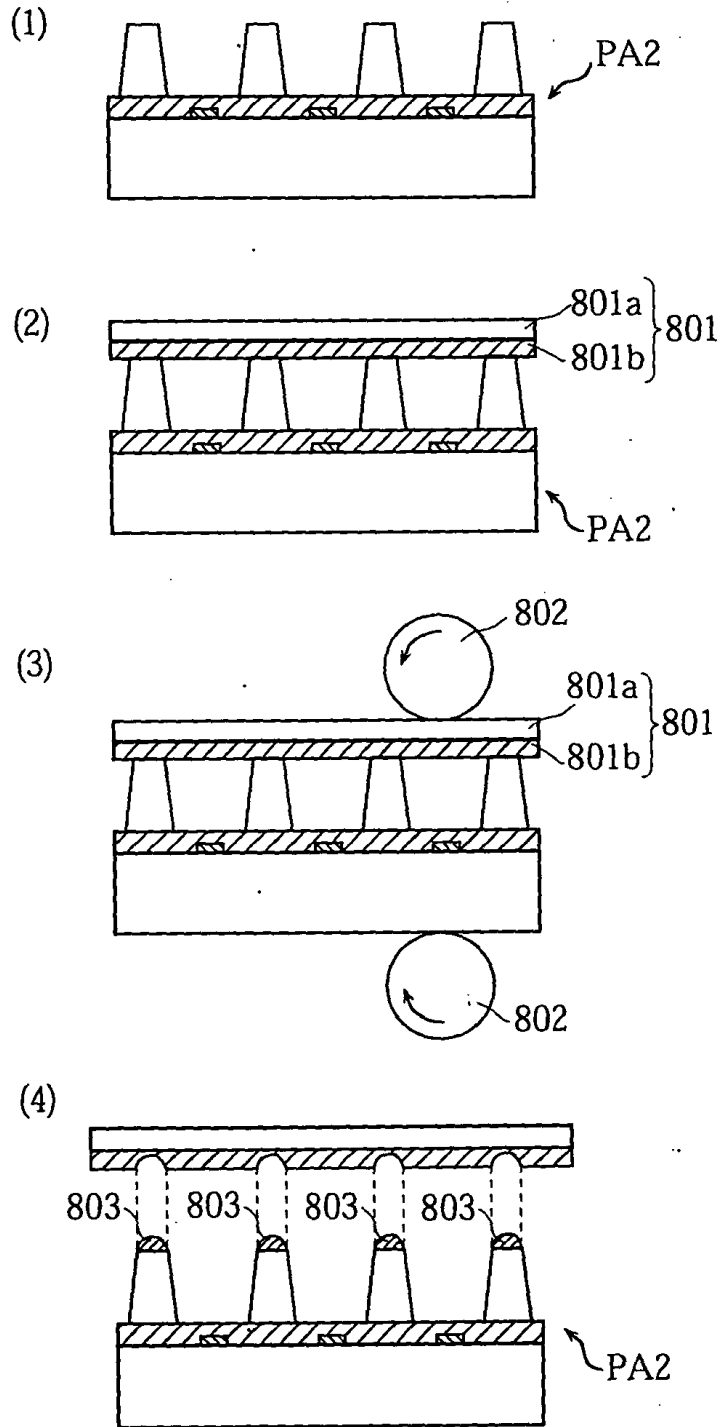


FIG. 28

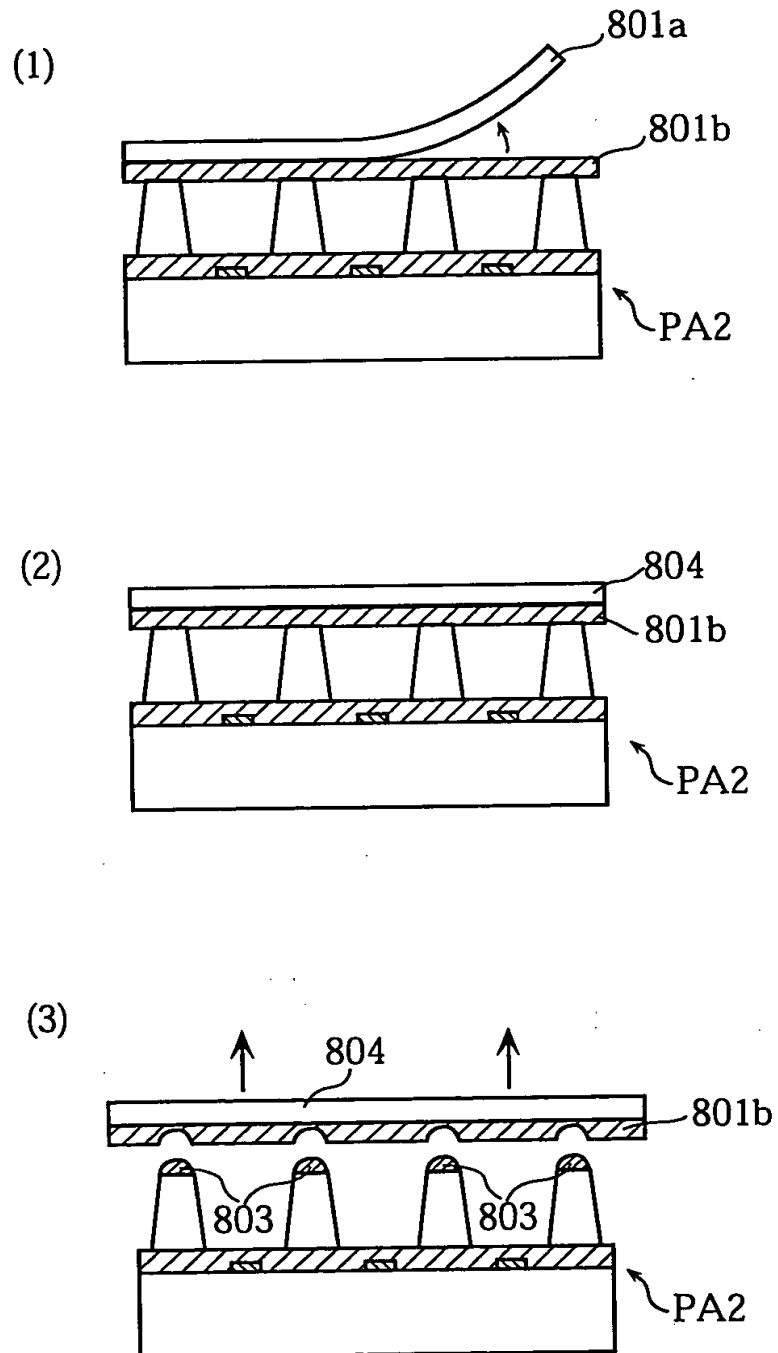


FIG. 29

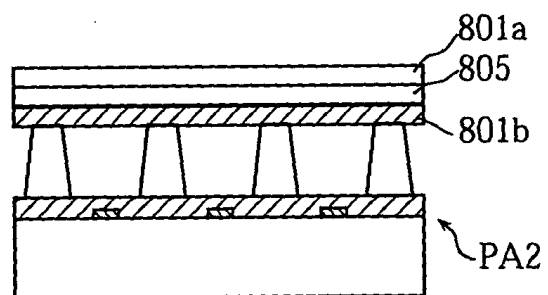


FIG. 30

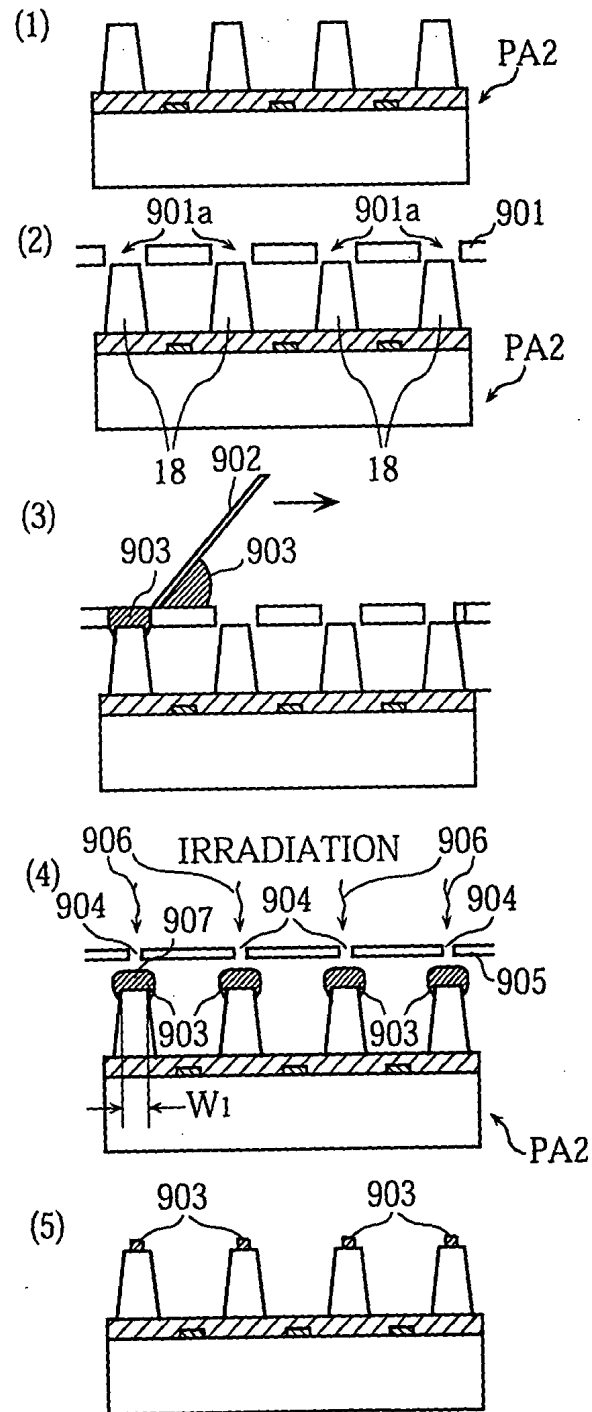


FIG. 31

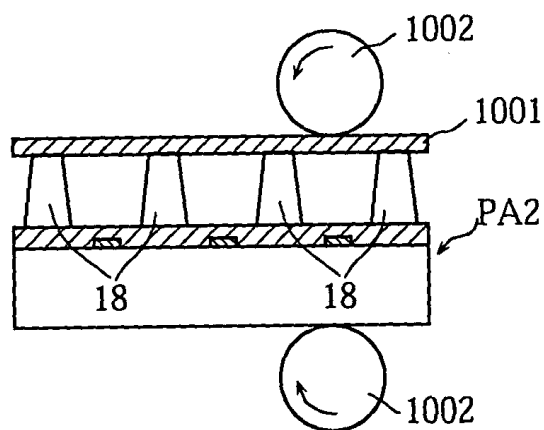


FIG. 32A

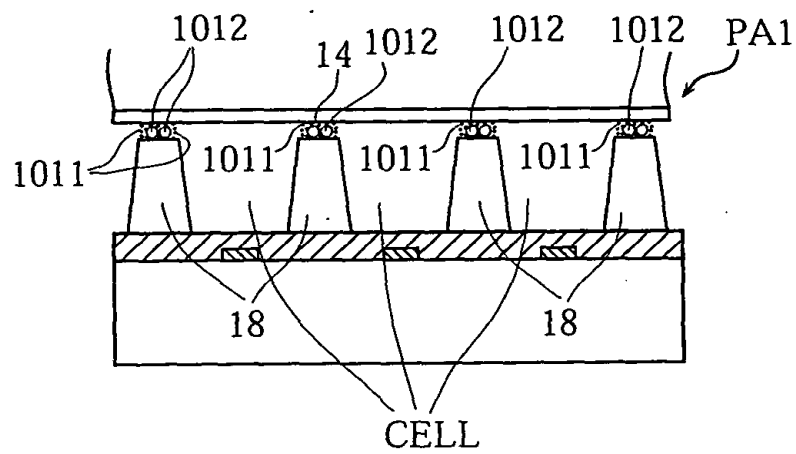


FIG. 32B

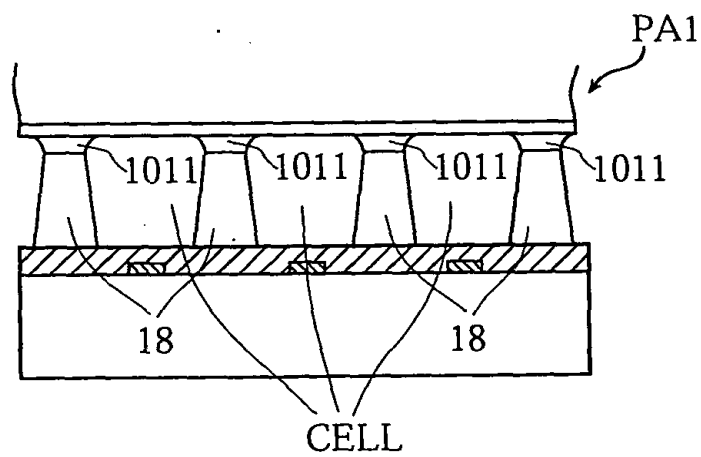


FIG. 33

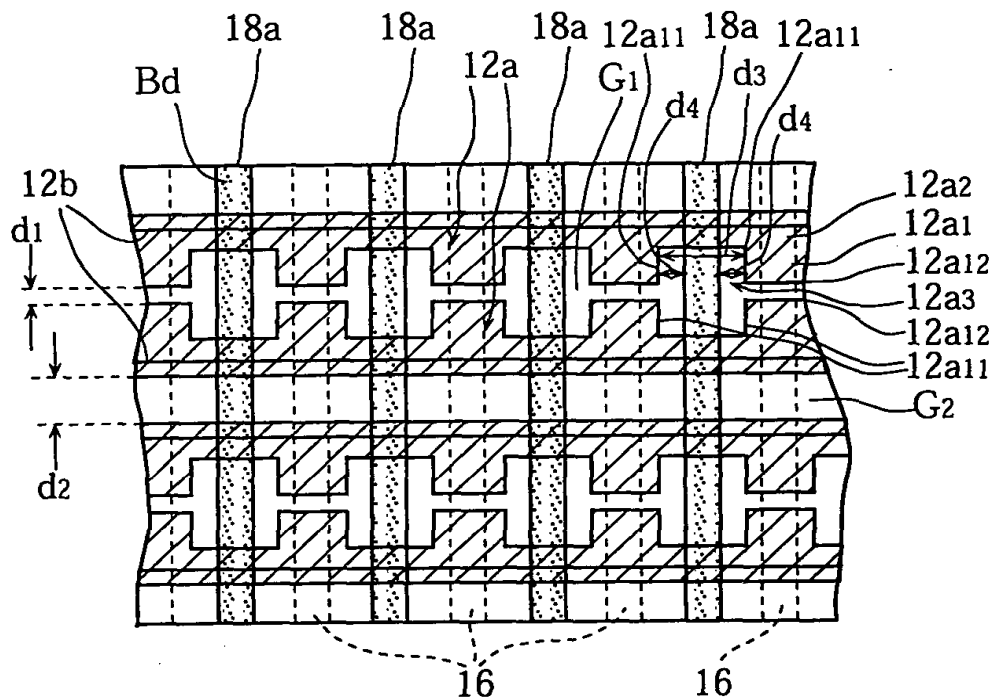
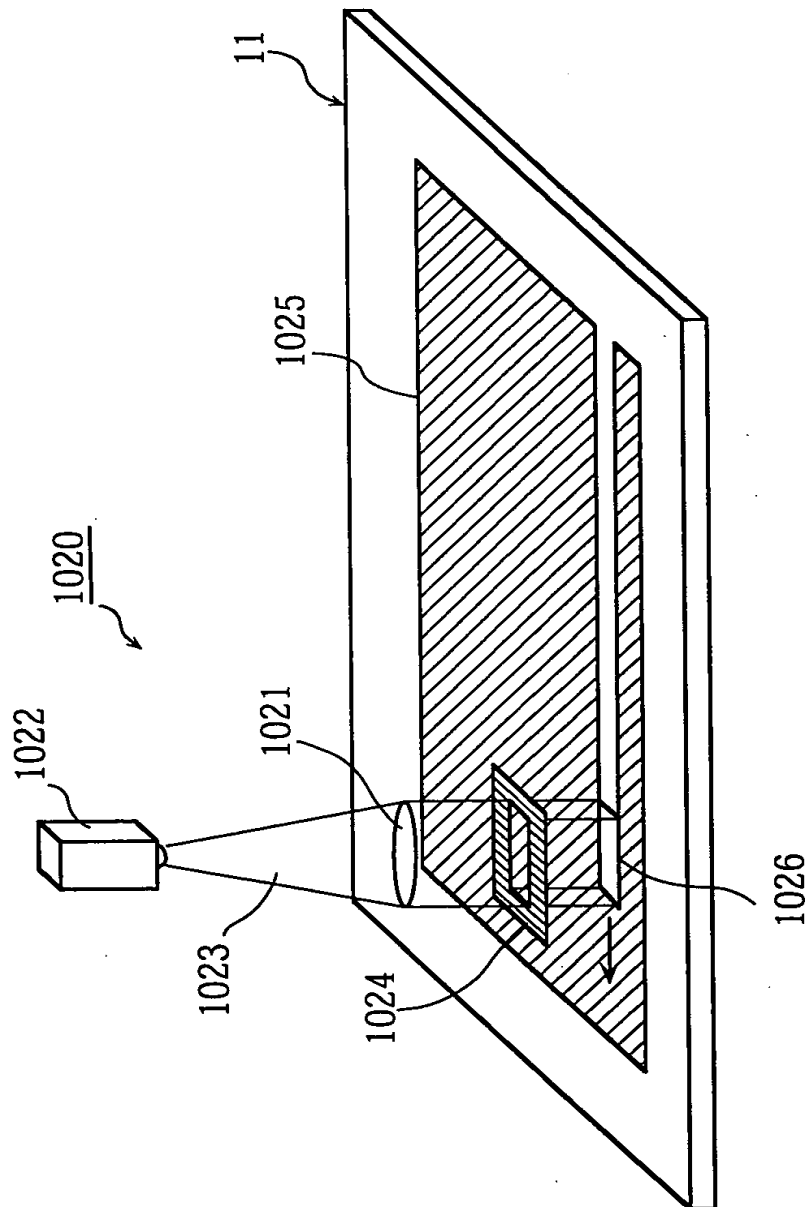
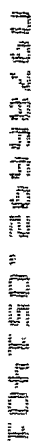


FIG. 34



[illegible]

THEOREM 1. Let $\{f_n\}$ be a sequence of functions in $L^1(\mathbb{R}^n)$ such that

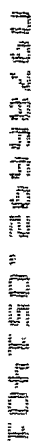


FIG. 39

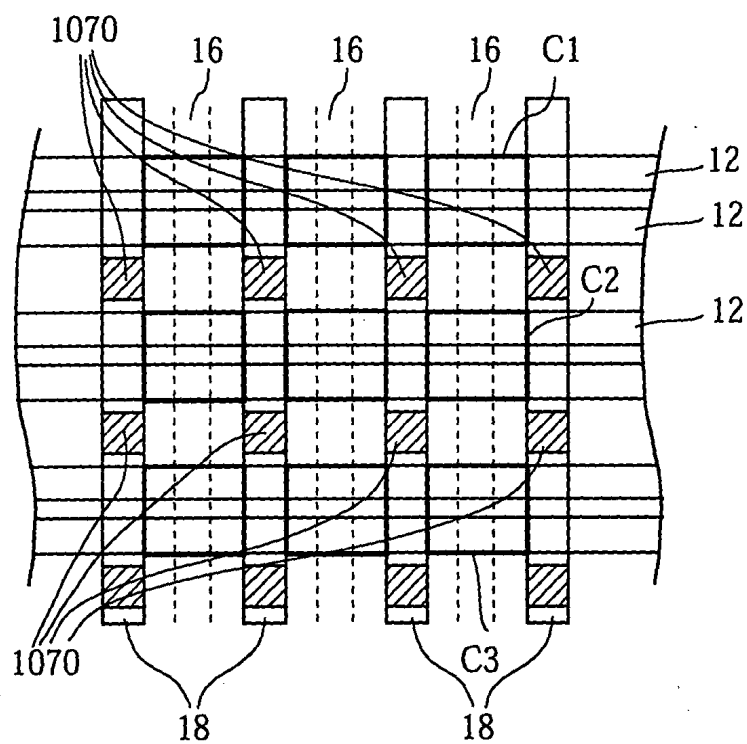


FIG. 40

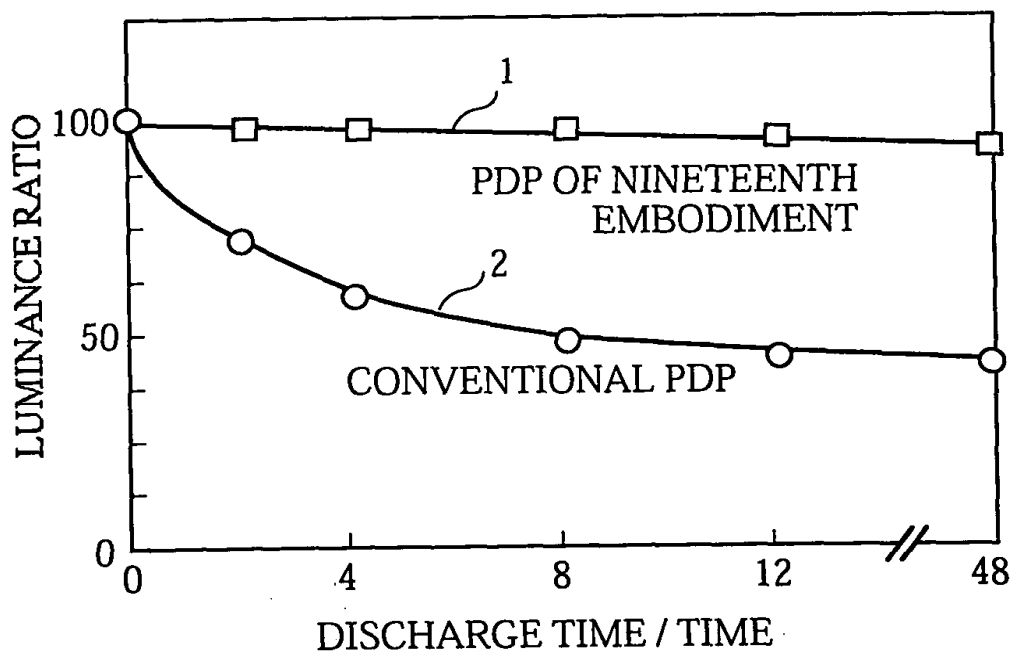


FIG. 41A

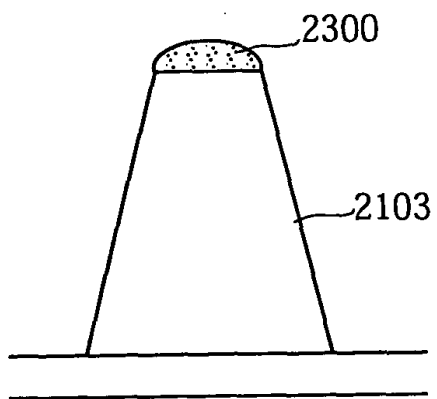


FIG. 41B

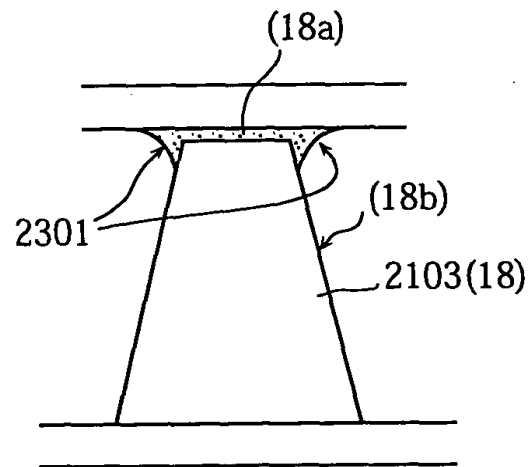


FIG. 42

